Shantou Huashan Electronic Devices Co.,Ltd.

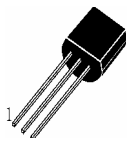
PNP SILICON TRANSISTOR

H984

APPLICATIONS

Low frequency power amplifier Applications.

TO-92



1—Emitter，E
2—Collector，C
3—Base，B

ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature…… -55~150℃

T_j——Junction Temperature……150℃

P_C——Collector Dissipation……600mW

V_{CBO}——Collector-Base Voltage……-60V

V_{CEO}——Collector-Emitter Voltage……-50V

V_{EBO}——Emitter-Base Voltage……-5V

I_C——Collector Current……-500mA

I_{CP}——Collector Current (Pulse)……-800mA

ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-60			V	I_C=-10μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	-50			V	I_C=-1mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	-5			V	I_E=-10μA，I_C=0
I_{CBO}	Collector Cut-off Current			-1.0	μA	V_{CB}=-40V, I_E=0
I_{EBO}	Emitter Cut-off Current			-1.0	μA	V_{EB}=-4V, I_C=0
$H_{FE(1)}$	DC Current Gain	60		320		V_{CE}=-5V, I_C=-50mA
$H_{FE(2)}$		35				V_{CE}=-5V, I_C=-400mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		-0.2	-0.6	V	I_C=-400mA, I_B=-40mA
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		-0.9	-1.2	V	I_C=-400mA, I_B=-40mA
f_T	Current Gain-Bandwidth Product		120		MHz	V_{CE}=-10V, I_C=-10mA
Cob	Output Capacitance		5		pF	V_{CB}=-10V, f=1MHz

h_{FE} Classification

D	E	F
60—120	1200—200	160—320